

M2708 8K (1K x 8) UV ERASABLE PROM

■ Extended Temperature Range:

-55°C to 100°C

■ Fast Programming: Typ. 100 sec. For All 8K Bits

■ Low Power During Programming

■ Access Time: 450 ns Max.

■ Standard Power Supplies:

+12V, +5V, -5V

Static: No Clocks Required

Inputs and Outputs TTL Compatible During Both Read and Program Modes

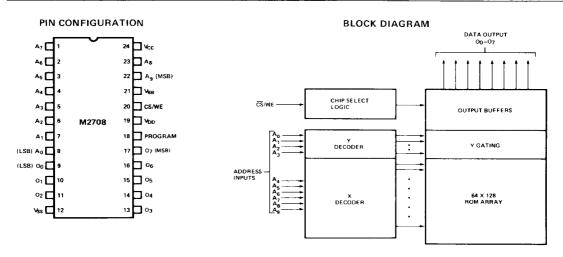
■ Three-State Output: OR-Tie Capability

■ Hermetic Package: 24 Pin DIP

The Intel M2708 is a high speed 8192 bit erasable and electrically reprogrammable ROM (EPROM) ideally suited where fast turn around and pattern experimentation are important requirements.

The M2708 is packaged in a 24-pin dual-in-line package with transparent lid. The transparent lid allows the user to expose the chip to ultraviolet light to erase the bit pattern. A new pattern can then be written into the devices.

The M2708 is fabricated with the time proven N-channel silicon gate technology.



PIN NAMES

A _Q ·A ₉	ADDRESS INPUTS
01-08	DATA OUTPUTS
CS/WE	CHIP SELECT/WRITE ENABLE INPUT

PIN CONNECTION DURING READ OR PROGRAM

	PIN NUMBER								
MODE	DATA I/O 9-11, 13-17	ADDRESS INPUTS 1-8, 22, 23	V _{SS}	PROGRAM 18	V _{DD}	CS/WE	V _{BB}	V _{CC}	
READ	Dout	Ain	GND	GND	+12	VIL	-5	+5	
DESELECT	HIGH IMPEDANCE	DON'T CARE	GND	GND	+12	ViH	-5	+5	
PROGRAM	D _{IN}	Ain	GND	PULSED Vihp	+12	VIHW	-5	+5	

MILITAR

Absolute Maximum Ratings*

Temperature Under Bias
Storage Temperature
V _{DD} With Respect to V _{BB} +20V to -0.3V
V _{CC} and V _{SS} With Respect to V _{BB} +15V to -0.3V
All Input or Output Voltages With Respect
to V _{BB} During Read
CS/WE Input With Respect to VBB
During Programming +20V to -0.3V
Program Input With Respect to V _{BB} +35V to -0 3V
Power Dissipation

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional eigeration of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

READ OPERATION

D.C. and Operating Characteristics

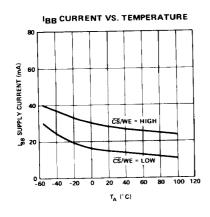
 $T_A = -55^{\circ} C$ to $100^{\circ} C$, $V_{CC} = +5V \pm 10\%$, $V_{DD} = +12V \pm 10\%$, $V_{BB}^{[1]} = -5V \pm 10\%$, $V_{SS} = 0V$, unless otherwise noted.

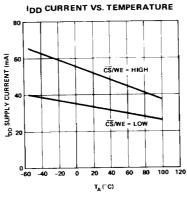
Symbol	Parameter	Min.	Typ. ^[2]	Max.	Unit	Conditions
LI	Address and Chip Select Input Sink Current	<u> </u>	1	10	μА	V_{IN} = 5.5 V or V_{IN} = V_{IL}
LO	Output Leakage Current		1	10	μΑ	V _{OUT} = 5.5 V, CS/WE = 5V
DD[3]	V _{DD} Supply Current	+	50	80	mA	Worst Case Supply Currents:
cc ^[3]	V _{CC} Supply Current		6	15	mA	All Inputs High
вв ^[3]	V _{BB} Supply Current		30	60	mA	CS/WE = 5V; TA = -55°C
/IL	Input Low Voltage	V _{SS}		0.65	٧	
/ _{IH}	Input High Voltage	3.0		V _{CC} +1	V	
/ _{OL}	Output Low Voltage			0.45	V	I _{OL} = 1.6mA
/ _{ОН1}	Output High Voltage	3.7			V	l _{OH} = -100μA
/ _{ОН2}	Output High Voltage	2.4			V	I _{OH} = -1mA
D	Power Dissipation			750	mW	T _A = 100°C

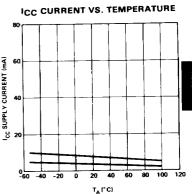
NOTES: 1. V_{BB} must be applied prior to V_{CC} and V_{DD}. V_{BB} must also be the last power supply switched off.

- 2. Typical values are for TA = 25°C and nominal supply voltages.
- The total power dissipation of the M2708 is specified at 750 mW. It is not calculated by summing the various currents (I_{DD}, I_{CC}, and I_{BB}) multiplied by their respective voltages since current paths exist between the various power supplies and V_{SS}. The I_{DD}, I_{CC}, and I_{BB} currents should be used to determine power supply capacity only.

Typical D.C. Characteristics







11-17

A.C. Characteristics

 $T_{A} = -55^{\circ}C$ to $100^{\circ}C$, $V_{CC} = +5V \pm 10\%$, $V_{DD} = +12V \pm 10\%$, $V_{BB} = -5V \pm 10\%$, $V_{SS} = 0V$, Unless Otherwise Noted.

Symbol	Parameter	Min.	Typ. [1]	Max.	Unit
†ACC	Address to Output Delay		280	450	ns
tco	Chip Select to Output Delay		60	120	ns
t _{DF}	Chip De-Select to Output Float	0		120	ns
t _{OH}	Address to Output Hold	0			ns

Note 1. Typical valves are for TA = 25°C and nominal supply voltages

Capacitance^[2] T_A = 25°C, f = 1MHz

Symbol	Parameter	Тур.	Max.	Unit	Conditions
CIN	Input Capacitance	4	6	рF	V _{IN} =0V
C _{OUT}	Output Capacitance	8	12	рF	V _{OUT} =0V

Note 2. This parameter is sampled and not 100% tested.

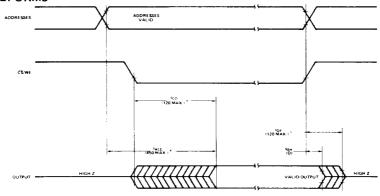
A.C. TEST CONDITIONS:

Output Load: 1 TTL gate and C₁ = 100 pF Input Rise and Fall Times: ≤20 ns

Timing Measurement Reference Levels: 0.8V and 2.8V for inputs; 0.8V and 2.4V for outputs

Input Pulse Levels: 0.65V to 3.0V

A.C. WAVEFORMS^[3]



- LUES ARE FUN....
 «HERE'S ONLY SAMPLED AND SAMPLED AND

ERASURE CHARACTERISTICS

The erasure characteristics of the M2708 are such that erasure begins to occur when exposed to light with wavelengths shorter than approximately 4000 Angstroms (Å). It should be noted that sunlight and certain types of fluorescent lamps have wavelengths in the 3000-4000Å range. Data show that constant exposure to room level fluorescent lighting could erase the typical M2708 in approximately 3 years, while it would take approximatley 1 week to cause erasure when exposed to direct sunlight. If the M2708 is to be exposed to these types of lighting conditions for extended periods of time, opaque labels are available from Intel which should be placed over the M2708 window to prevent unintentional erasure.

The recommended erasure procedure (see Data Catalog PROM/ROM Programming Instructions section) for the M2708 is exposure to shortwave ultraviolet light which has a wavelength of 2537 Angstroms (Å). The integrated dose (i.e., UV intensity X exposure time) for erasure should be a minimum of 15 W-sec/cm². The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with a 1200 μ W/cm² power rating. The M2708 should be placed within 1 inch of the lamp tubes during erasure. Some lamps have a filter on their tubes which should be removed before erasure.